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AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph spanning pages 2-3 (beginning on page 2, line 30) with the following rewritten version:

-- A method for drying substrate of claim 1 houses substrates within a processing vessel, and dries a surface of each substrate by relatively lowering a fluid face of cleaning fluid within a processing vessel with respect to the substrates and by introducing the cleaning fluid within the processing vessel, the method comprises the steps of,

Introducing introducing drying fluid under a liquid condition within the processing vessel, and

Forming forming liquid drops of drying fluid and supplying the liquid drops onto the fluid face of the cleaning fluid using a nozzle. --

Please replace the paragraph beginning on page 3, line 8 with the following rewritten version:

-- Wherein, the <u>The</u> liquid drops is preferable to have preferably have a diameter which is greater than 100 μ m and equal to or less than 1 mm. The liquid drops is more preferable to preferably have a diameter which is greater than 100 μ m and equal to or less than 200 μ m. --

Please replace the paragraph beginning at page 3, line 12 with the following rewritten version:

-- [[A]] The method for drying substrate of claim 2 houses can house the substrates within the processing vessel in an inclined condition by a predetermined angle, and supplies supply the liquid drops of drying fluid using the nozzle in a direction which is the same direction of the inclined substrates: --

Please replace the paragraph beginning at page 3, line 17 with the following rewritten version:

-- Wherein, the <u>The</u> inclination angle is preferable preferably to be greater than 0° and equal to or less than 30°. The inclination angle is more preferable preferably to be equal to or greater than 3° and equal to or less than 5°. --

Please replace the paragraph beginning at page 3, line 21 with the following rewritten version:

-- [[A]] The method for drying substrate of claim 3 can determine an introduction direction of the drying fluid into the processing vessel and determines determine an introduction initial speed of the drying fluid so as to expand the drying fluid up to the entire width of the substrates on the fluid surface of the cleaning fluid. --

Please replace the paragraph beginning at page 3, line 26 with the following rewritten version:

-- Wherein, the <u>The</u> introduction initial speed is <u>preferable to be preferably</u> equal to or greater than 10 m/sec and equal to or less than 330 m/sec. The introduction initial speed is more <u>preferable to be preferably</u> equal to or greater than 50 m/sec and equal to or less than 150 m/sec. --

Please replace the paragraph beginning at page 3, line 31 with the following rewritten version:

-- [[A]] <u>The</u> method for drying substrate of claim 4 supplies can supply inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 4, line 1 with the following rewritten version:

-- [[A]] <u>The</u> method for drying substrate <u>of claim 5 increases</u> can increase the supplying quantity of the drying fluid and/or the inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 4, line 5 with the following rewritten version:

-- [[A]] The method for drying substrate of claim 6 changes can change a supporting position of the substrates following exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 4, line 8 with the following rewritten version:

-- [[A]] <u>The</u> method for drying substrate of claim 7 can makes make the interior of the processing vessel to be inert gas environment prior to exhausting of cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 4, line 11 with the following rewritten version:

-- [[A]] The method for drying substrate of claim 8 carries can carry out the cleaning process and the following drying processing under a room temperature. --

Please replace the paragraph beginning at page 4, line 14 with the following rewritten version:

-- [[A]] <u>The</u> method for drying substrate of claim 9 flows can flow the drying fluid by the pressure of inert gas which is supplied to the nozzle. --

Please replace the paragraph beginning at page 4, line 16 with the following rewritten version:

-- A device for drying substrate of elaim 10 supports substrates within a processing vessel by supporting means, and dries a surface of each substrate by relatively lowering a fluid face of cleaning fluid within a processing vessel with respect to the substrates and by introducing the cleaning drying fluid within the processing vessel, the device compromises,

Drying drying fluid supplying means for introducing drying fluid under a liquid condition within the processing vessel, for forming liquid drops of drying fluid using a nozzle, and for supplying the liquid drops of drying fluid onto the fluid face of the cleaning fluid using a nozzle. --

Please replace the paragraph beginning at page 4, line 27 with the following rewritten version:

-- Wherein, the <u>The</u> liquid drops is preferable to preferably have a diameter which is greater than 100 μm and equal to or less than 1 mm. The liquid drops is more preferable to preferably have a diameter which is greater than 100 μm and equal to or less than 200 μm. --

Please replace the paragraph spanning pages 4 and 5 (beginning on page 4, line 31) with the following rewritten version:

-- [[A]] In the device for drying substrate of claim 11, wherein the supporting means is the can be means for supporting the substrates within the processing vessel in an inclined condition by a predetermined angle, and the nozzle is can be a nozzle for supplying the liquid drops of drying fluid using the nozzle in a direction which is the same direction of the inclined substrates. --

Please replace the paragraph beginning on page 5, line 3 with the following rewritten version:

-- Wherein, the <u>The</u> inclination angle is preferable preferably to be greater than 0° and equal to or less than 30°. The inclination angle is more preferable preferably to be equal to or greater than 3° and equal to or less than 5°. --

Please replace the paragraph beginning at page 5, line 7 with the following rewritten version:

-- [[A]] In the device for drying substrate of claim 12, wherein the drying fluid supplying means is can be a means for determining an introduction direction of the drying fluid into the processing vessel and determines determining an introduction initial speed of the drying fluid so as to expand the drying fluid up to the entire width of the substrates on the fluid surface of the cleaning fluid. --

Please replace the paragraph beginning at page 5, line 13 with the following rewritten version:

-- Wherein, the <u>The</u> introduction initial speed is <u>preferable to be preferably</u> equal to or greater than 10 m/sec and equal to or less than 330 m/sec. The introduction initial speed is more <u>preferable to be preferably</u> equal to or greater than 50 m/sec and equal to or less than 150 m/sec. --

Please replace the paragraph beginning at page 5, line 18 with the following rewritten version:

-- [[A]] <u>The</u> device for drying substrate of claim 13 can further comprises comprise inert gas supplying means for supplying inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 5, line 22 with the following rewritten version:

-- [[A]] The device for drying substrate of claim 14 can further comprises comprise supplying quantity control means for increasing the supplying quantity of the drying fluid and/or the inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 5, line 27 with the following rewritten version:

-- [[A]] In the device for drying substrate of claim 15, wherein the supporting means is can be a means having a cleaning fluid introduction groove which follows in a lower ward direction with respect to the substrate supporting section. --

Please replace the paragraph spanning pages 5 and 6 (beginning on page 5, line 31) with the following rewritten version:

-- [[A]] In the device for drying substrate of claim 16, wherein the supporting means is can be a pair of supporting means for selectively supporting different positions of the substrates which positions are different from one another, and further comprises comprise supporting position control means for changing the supporting position of the substrates by the supporting means following exhausting of the cleaning fluid from the processing vessel.

Please replace the paragraph beginning at page 6, line 4 with the following rewritten version:

-- [[A]] <u>The</u> device for drying substrate of claim 17 can further comprises comprise environment determination means for making the interior of the processing vessel to be inert gas environment prior to exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 6, line 8 with the following rewritten version:

-- [[A]] The device for drying substrate of claim 18 can further comprises comprise nozzle position control means for moving the nozzle towards the substrate following exhausting of the cleaning fluid from the processing vessel. --

Please replace the paragraph beginning at page 6, line 12 with the following rewritten version:

-- Wherein the <u>The</u> moveable extent of the nozzle by the nozzle position control means is preferable to be preferably greater than 0 mm and equal to or less than 500 mm. The moveable extent is more preferable to be preferably equal to or greater than 250 mm and equal to or less than 350 mm. --

Please replace the paragraph beginning at page 6, line 17 with the following rewritten version:

-- [[A]] The device for drying substrate of claim-19 can further comprising comprise circulation means for circulating the drying fluid when ejection is not carried out. --

Please replace the paragraph beginning at page 6, line 20 with the following rewritten version:

-- [[A]] In the device for drying substrate of claim 20, wherein a number of nozzles is can be determined in response to response to the size of the substrate and the pitch of the substrates. --

Appl. No. 09/936,618 Amendment dated December 23, 2003 Reply to Office Action of July 3, 2003

Please replace the paragraph beginning at page 6, line 23 with the following rewritten version:

-- [[A]] In the device for drying substrate of claim 21, wherein the nozzle can has have drying fluid ejection holes a number of which is greater than the number of the substrates by 1 which substrates are dried simultaneously. --

Please replace the paragraph beginning at page 6, line 27 with the following rewritten version:

-- [[A]] The device for drying substrate of claim 22 can further comprises comprise inert gas supplying means for supplying inert gas to the nozzle so as to flow the drying fluid by the pressure of inert gas. --

Please replace the paragraph spanning pages 6 and 7 (beginning on page 6, line 30) with the following rewritten version:

-- When the method for drying substrate of claim 1 is employed, the method can houses house substrates within the processing vessel, and dries dry the surface of each substrate by relatively lowering the fluid face of cleaning fluid within the processing vessel with respect to the substrate and by introducing the drying fluid within the processing vessel.

Please replace the paragraph beginning at page 8, line 1 with the following rewritten version:

-- When the method for drying substrate of claim 2 is employed, the method can houses house the substrates within the processing vessel in an inclined condition by a predetermined angle, and supplies supply the liquid drops of drying fluid using the nozzle in a direction which is the same direction of the inclined substrates. Therefore, when each substrate has a pattern on one face and when the pattern formed face of a plurality of substrates are positioned In in the same side, exhausting of the cleaning fluid is easily performed which is introduced within the inner section of the pattern so that more rapid and better drying is realized. --

Please replace the paragraph spanning pages 8 and 9 (beginning on page 8, line 20 with the following rewritten version:

-- When the method for drying substrate of claim 3 is employed, the method can determines determine an introduction direction of the drying fluid into the processing vessel and determines determine an introduction initial speed of the drying fluid so as to expand the drying fluid up to the entire width of the substrates on the fluid surface of the cleaning fluid. Therefore, even when the substrates become enlarged in diameter and/or when the interval between the substrates is decreased, the liquid drops of drying fluid are smoothly supplied into the gap between the substrates and the liquid layer of the drying fluid is continuously formed on the liquid face of the cleaning fluid so that rapid drying of the substrates is realized without drying marks. Further, the density of the drying fluid is not needed to be raised too high and the temperature of the drying fluid is not needed to be raised too high, so that the running cost is decreased. Also, though the drying fluid has explosiveness due to the inflammability of the drying fluid when the drying fluid is mixed with air, the explosiveness can be suppressed so that safety is improved. --

Please replace the paragraph beginning at page 9, line 16 with the following rewritten version:

-- When the method for drying substrate of claim 4 is employed, the method can supplies supply inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. Therefore, the interior of the processing vessel becomes negative pressured condition following exhausting of the cleaning fluid so that particles are prevented from intruding from the exterior. --

Please replace the paragraph beginning at page 9, line 22 with the following rewritten version:

-- When the method for drying substrate of claim 5 is employed, the method can increases increase the supplying quantity of the drying fluid and/or the inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel.

Therefore, the liquid drops of the drying fluid are securely supplied to the liquid face of the cleaning fluid by increasing the supplying quantity following exhausting of the cleaning fluid

so that the thickness of the liquid layer of the drying fluid on the cleaning fluid is continuously maintained to be equal to or greater than a predetermined thickness. --

Please replace the paragraph spanning pages 9 and 10 (beginning at page 9, line 32) with the following rewritten version:

-- When the method for drying substrate of claim 6 is employed, the method can changes change supporting position of the substrates following exhausting of the cleaning fluid from the processing vessel. Therefore, the supporting position of the substrates is also rapidly and securely dried. --

Please replace the paragraph beginning at page 10, line 3 with the following rewritten version:

-- When the method for drying substrate of claim 7 is employed, the method can makes make the interior of the processing vessel to be inert gas environment prior to exhausting of the cleaning fluid from the processing vessel. Therefore, generation of water mark on the surface of the substrate is greatly suppressed. --

Please replace the paragraph beginning at page 10, line 8 with the following rewritten version:

-- When the method for drying substrate of claim 8 is employed, the method can earries carry out the cleaning process and the following drying processing under a room temperature. Therefore, heating process is not needed at all, so that simplification in arrangement in entire system is realized and that safety is improved. --

Please replace the paragraph beginning at page 10, line 13 with the following rewritten version:

-- When the method for drying substrate of claim 9 is employed, the method can flows flow the drying fluid by the pressure of inert gas which is supplied to the nozzle. Therefore, driving section for supplying the drying fluid is not needed at all, and cleanness is improved by preventing particles from mixing and intruding. --

Please replace the paragraph beginning at page 10, line 18 with the following rewritten version:

-- When the device for drying substrate of claim 10 is employed, the device can supports support substrates within a processing vessel by supporting means, and dries dry a surface of each substrate by relatively lowering a fluid face of cleaning fluid within a processing vessel with respect to the substrate and by introducing the cleaning fluid within the processing vessel. --

Please replace the paragraph beginning at page 11, line 23 with the following rewritten version:

-- When the device for drying substrate of claim 11 is employed, the device can employs employ the supporting means which supports the substrates within the processing vessel in an inclined condition by a predetermined angle, and the device can employs employ the nozzle which supplies the liquid drops of drying fluid using the nozzle in a direction which is the same direction of the inclined substrates. --

Please replace the paragraph beginning at page 12, line 10 with the following rewritten version:

-- When the device for drying substrate of claim 12 is employed, the device can employs employ the drying fluid supplying means which determines an introduction direction of the drying fluid into the processing vessel and determines an introduction initial speed of the drying fluid so as to expand the drying fluid up to the entire width of the substrates on the fluid surface of the cleaning fluid. --

Please replace the paragraph beginning at page 13, line 7 with the following rewritten version:

-- When the device for drying substrate of claim 13 is employed, the device can further emprises comprise inert gas supplying means for supplying inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. Therefore, the interior of the processing vessel becomes negative pressured condition following exhausting of the cleaning fluid so that particles are prevented from intruding from the exterior. --

Please replace the paragraph beginning at page 13, line 14 with the following rewritten version:

-- When the device for drying substrate of claim 14 is employed, the device can further comprises comprise supplying quantity control means for increasing the supplying quantity of the drying fluid and/or the inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel. Therefore, the liquid drops of the drying fluid are securely supplied to the liquid face of the cleaning fluid by increasing the supplying quantity following exhausting of the cleaning fluid so that the thickness of the liquid layer of the drying fluid on the cleaning fluid is continuously maintained to be equal to or greater than a predetermined thickness. --

Please replace the paragraph beginning at page 13, line 24 with the following rewritten version:

-- When the device for drying substrate of claim 15 is employed, the device can employs employ the supporting means which have a cleaning fluid introduction groove which follows in a lower ward direction with respect to the substrate supporting section. Therefore, drainage of the cleaning fluid at the substrate supporting section is improved. --

Please replace the paragraph spanning pages 13 and 14 (beginning on page 13, line 30) with the following rewritten version:

-- When the device for drying substrate of claim 16 is employed, the device can employs employ a pair of supporting means for selectively supporting different positions of the substrates which positions are different from one another, and the device can further comprises comprise supporting position control means for changing the supporting position of the substrates by the supporting means following exhausting of the cleaning fluid from the processing vessel. Therefore, the supporting position of the substrate is also dried rapidly and securely. --

Please replace the paragraph beginning at page 14, line 4 with the following rewritten version:

-- When the device for drying substrate of claim 17 is employed, the device can further comprises comprise environment determination means for making the interior of the processing vessel to be inert gas environment prior to exhausting of the cleaning fluid from the processing vessel. Therefore, generation of water mark on the surface of the substrate is greatly suppressed. --

Please replace the paragraph beginning at page 14, line 10 with the following rewritten version:

-- When the device for drying substrate of claim-18 is employed, the device can further comprises comprise nozzle position control means for moving the nozzle towards the substrates following exhausting of the cleaning fluid from the processing vessel. Therefore, the drying fluid with sufficient quantity is supplied onto the liquid face of the cleaning fluid without changing the introduction initial speed and the introduction flowing quantity of the liquid drops of the drying fluid. --

Please replace the paragraph spanning pages 14 and 15 (beginning on page 14, line 30) with the following rewritten version:

-- When the device for drying substrate of claim 19 is employed, the device can further comprising comprise circulation means for circulating the drying fluid when ejection is not carried out. Therefore, the pressure of the space in which the drying fluid exists is always determined to be greater than the pressure in exterior so as to prevent particles from intruding from exterior, and the usage quantity of the drying fluid is reduced so as to decrease the running cost. --

Please replace the paragraph beginning at page 15, line 3 with the following rewritten version:

-- When the device for drying substrate of claim 20 is employed, the device can employs employ the nozzles a number of which is determined in response to response to the size of the substrate and the pitch of the substrates. Therefore, uniformly uniform drying is realized on the entire face of the substrate. --

Please replace the paragraph beginning at page 15, line 8 with the following rewritten version:

-- When the device for drying substrate of claim 21 is employed, the device can employs employ the nozzle which has drying fluid ejection holes a number of which is greater than the number of the substrates by 1 which substrates are dried simultaneously. Therefore, liquid drops of the drying fluid are supplied to every gap between the substrates and the outer side of the substrates which are positioned at both ends so as to dry the entire surface of each substrate rapidly and uniformly (without generation of water mark). --

Please replace the paragraph beginning at page 15, line 17 with the following rewritten version:

-- When the device for drying substrate of claim 22 is employed, the device can further comprises comprise inert gas supplying means for supplying inert gas to the nozzle so as to flow the drying fluid by the pressure of inert gas. Therefore, driving section for supplying the drying fluid is not needed at all, and cleanness is improved by preventing particles from mixing and intruding. --

Please replace the paragraph beginning at page 17, line 14 with the following rewritten version:

-- The first substrate supporting section 3 has a main body member 3a and a plurality of supporting grooves 3b having a cross sectional V-shape formed on the upper face of the main body member 3a, as is illustrated in Fig. 2. It is preferable that a slit 3c is further provided which elongates downward from the bottom section of each supporting groove 3b so as to improve drainage. The slit 3c can be considered to be a cleaning fluid introduction groove. It is more preferable that a round hole 3d is provided which is connected to the bottom section of the slit 3c so as to further improve drainage. --